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(54) **ETCH STOP IN A DEP-ETCH-DEP PROCESS**

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(57) **ABSTRACT**

Described herein is a method of forming semiconductor devices. The method comprises depositing an etch stop layer of titanium aluminum carbide in a cavity of a semiconductor device; depositing a first layer of metal on the etch stop layer; etching the first layer of metal to create an etch-modified surface of the first layer of metal; and depositing a second layer of metal on the etch-modified surface of the first layer of metal.

